PN-series AlGaInP LED chip

Features:

- (1) High luminous intensity
- (2) Long operation life
- (3) 100% probing test

Characteristics:

- (1) Size
 - Chip size: 10 mil x 10 mil ($254\pm25 \ \mu m \ x \ 254\pm25 \ \mu m$) Chip thickness: 6.7mil ($170\pm25 \ \mu m$) N bonding pad: 4.0 mil ($100\pm10 \ \mu m$)
- (2) Bonding pad : Au alloy
- (3) Structure
 - Refer to drawing

Electro-optical characteristics:



P-electrode

Parameter	Symbol		Condition	Min.	Тур.	Max.	Unit	
Forward voltage	$V_{\rm f1}$		$I_{\rm f}\!=10uA$	1.3			V	
	V_{f2}		$I_f\!=20mA$		2.1	2.5	V	
Reverse current	I _r		$V_r = 10V$			5	uA	
Peak wavelength	$\lambda_{ m p}$		$I_f\!=20mA$		611		nm	
Dominant wavelength ⁽¹⁾	λ_d		$I_f\!=20mA$	600	605	610	nm	
Spectra half-width	Δλ		$I_f\!=20mA$		18		nm	
Luminous intensity ⁽²⁾⁽³⁾		E13		350				
	Iv	E14		400			mcd	
		E15		450				

(1) Basically, wavelength uniformity is $\lambda_d \pm 5$ nm; however, customers' special requirements are also welcome.

(2) Customer's special requirements are also welcome.

(3) Luminous intensity is measured by EPISTAR's equipment on bare chips.





Fig-1 Relative Luminous Intensity vs. Forward Current.

Fig-2 Forward Current vs. Forward Voltage.

Note : Above L-I and I-V are measured under TO-18 form and pulse current.

Absolute maximum ratings:

Parameter	Symbol	Condition	Rating	Unit
Forward DC current	If	T _a =25°C	≤ 50	mA
Reverse voltage	Vr	T _a =25°C	≤ 10	V
Junction temperature	Tj		≤ 115	°C
		chip	-40 ~ +85	°C
Storage temperature	T _{stg}	chip-on-tape/storage	0 ~ 40	°C
		chip-on-tape/transportation	-20 ~ +65	°C
Temperature during packaging			280(<10 sec)	°C





Fig-3 Maximum Driving Forward DC Current vs. Ambient Temperature. Derating Based on $T_i(max) = 115 \ ^{o}C$

Applications:

- Traffic signal
- Backlighting
- Signage and channel letter
- Portable light source
- Decorating and entertainment lighting
- Architectural lighting
- Outdoor/Indoor applications